

Power Matters.™

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2N3878 (#23150)

Overview

Diagrams

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$			2.00	V
DC Current Gain	HFE	50.00		200.00	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	$V_{BR(CBO)}$			120.00	V
Collector Current (dc)	I_C			7.00	A
Collector-Emitter Voltage (Base Open)	V_{CEO}			50.00	V
Emitter-Base Voltage (Collector Open)	V_{EBO}			7.00	V
Power Dissipation, Total	P_T			35.00	W

This part can be found in the following product categories:

- ▶ Discretes ▶ Transistors ▶ BJT(BiPolar Junction Transistor) ▶ **FNP** Transistor
- ▶ Non-Radiation Hardened Devices ▶ Transistors ▶ BJT(BiPolar Junction Transistor) ▶ **NPN** Transistor

Related Links

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